

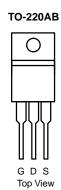
N-Channel 130 V (D-S) 175 °C MOSFET

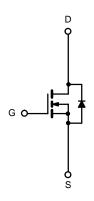
PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)	
130	0.0033 at V _{GS} = 10 V	160 ^a	

FEATURES

- TrenchFET® Power MOSFET
- New Package with Low Thermal Resistance
- 100 % R_g Tested







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	130	V		
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current (T = 175 °C)	T _C = 25 °C	I-	160 ^a	A	
Continuous Drain Current (T _J = 175 °C)	T _C = 125 °C	I _D	115 ^a		
Pulsed Drain Current		I _{DM}	580	7 ^	
Avalanche Current	I _{AR}	98			
Repetitive Avalanche Energy ^b	L = 0.1 mH	E _{AR}	1500	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	В	378 ^c	W	
Maximum i owei Dissipation	T _A = 25 °C	P _D 4.39	4.39	v v	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Limit	Unit	
Junction-to-Ambient	PCB Mount (TO-263) ^d	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/VV	

Notes:

- a. Package limited.
- b. Duty cycle ≤ 1 %.
- c. See SOA curve for voltage derating.
 d. When mounted on 1" square PCB (FR-4 material).

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	130			V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V			1	
	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	160			Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V, I _D = 20 A		0.0033	0.0042	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.0068	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.0112	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A	68			S
Dynamic ^b	•			•		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		7920		pF
Output Capacitance	C _{oss}			830		
Reverse Transfer Capacitance	C _{rss}			110		
Total Gate Charge ^c	Qg			110	150	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 85 \text{ A}$		46		
Gate-Drain Charge ^c	Q _{gd}			24		
Gate Resistance	R _g		1.0		6.2	Ω
Turn-On Delay Time ^c	t _{d(on)}			22	33	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 0.6 Ω I_D \cong 85 A, V_{GEN} = 10 V, R_g = 2.5 Ω		102	180	ns
Turn-Off Delay Time ^c	t _{d(off)}			53	85	
Fall Time ^c	t _f			18	35	
Source-Drain Diode Ratings and Cha	aracteristics -	Γ _C = 25 °C ^b				
Continuous Current	I _S				158	۸
Pulsed Current	I _{SM}				580	Α
Forward Voltage ^a	V _{SD}	I _F = 85 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}			75	148	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 50 A, dl/dt = 100 A/μs		5.5	10	Α
Reverse Recovery Charge	Q _{rr}			0.18	0.33	μС

Notes:

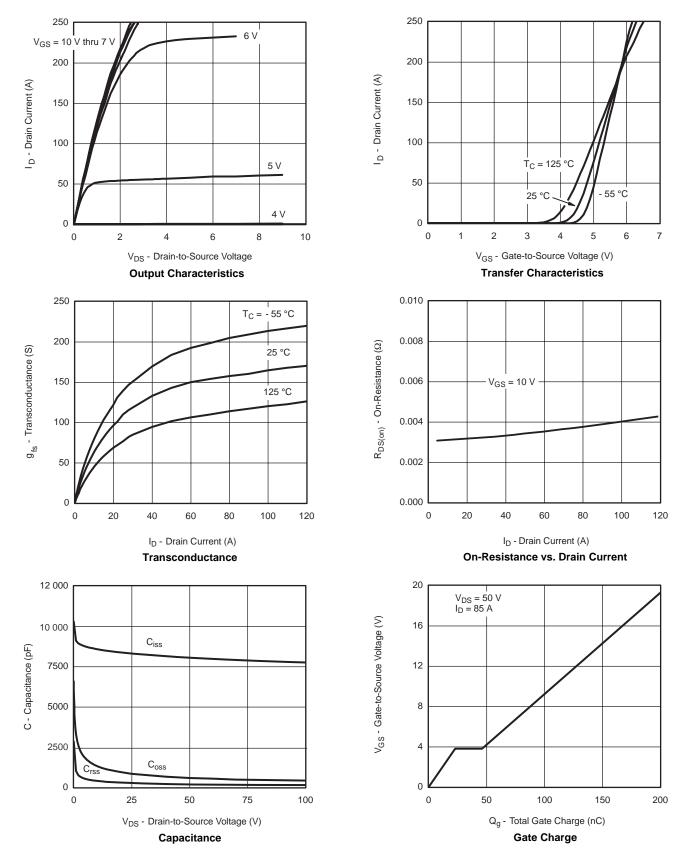
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





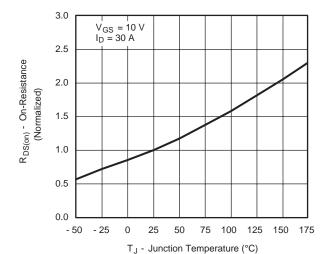
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



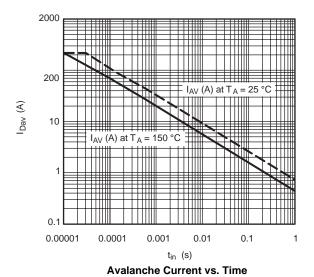


Din-Tek SEMICONDUCTOR

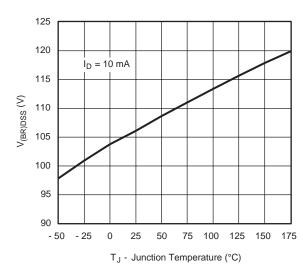
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On-Resistance vs. Junction Temperature



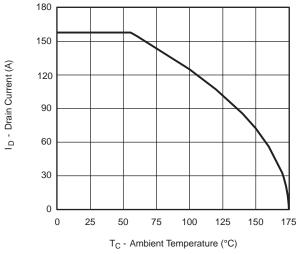
Source-Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature



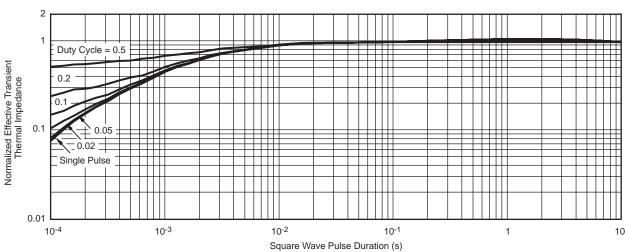
THERMAL RATINGS



300 I_D - Drain Current (A) by R_{DS(on)*} 10 T_C = 25 °C Single Pulse 0.1 0.1 1000 10 130 V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified Safe Operating Area

1000

Maximum Avalanche and Drain Current vs. Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case





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